

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
150V	6.7mΩ@10V	130A

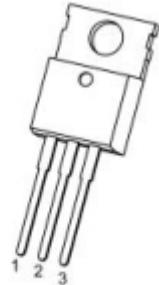
Feature

- Fast Switching
- Low Gate Charge and Rdson
- 100% Single Pulse avalanche energy Test

Applications

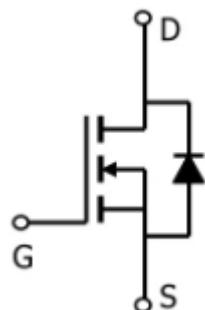
- Power switching application
- DC-DC Converter
- Power Management

Package

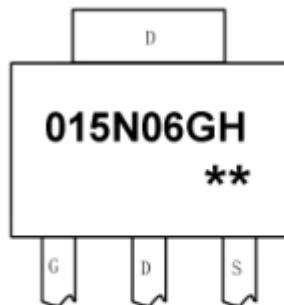


TO-220-3L-C(1:G 2:D 3:S)

Circuit diagram



Marking



015N06GH : Product code
****** : Week code

Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous drain current ($T_c = 25^\circ\text{C}$)	I_D	130	W
Pulsed Drain Current	I_{DM}	520	A
Power Dissipation ($T_c = 25^\circ\text{C}$)	P_D	280	W
Single Pulse Avalanche Energy ¹	E_{AS}	1056	mJ
Thermal Resistance Junction- Case	$R_{\theta JC}$	0.44	$^\circ\text{C}/\text{W}$
Operation and storage temperature	$T_{STG}, T_J,$	-55~+150	$^\circ\text{C}$

Electrical characteristics

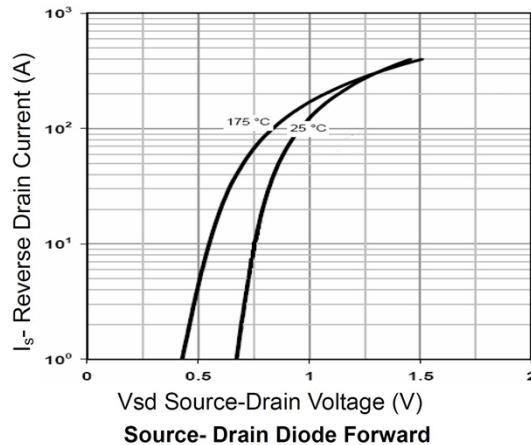
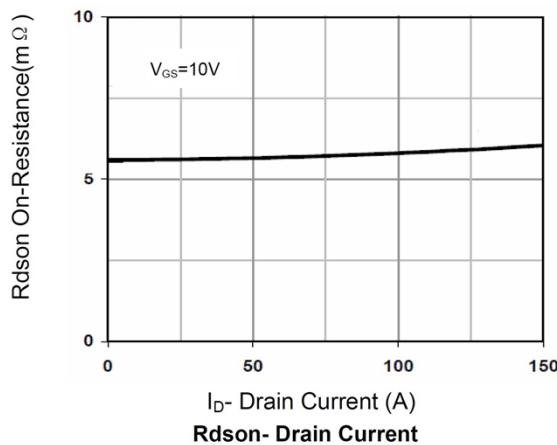
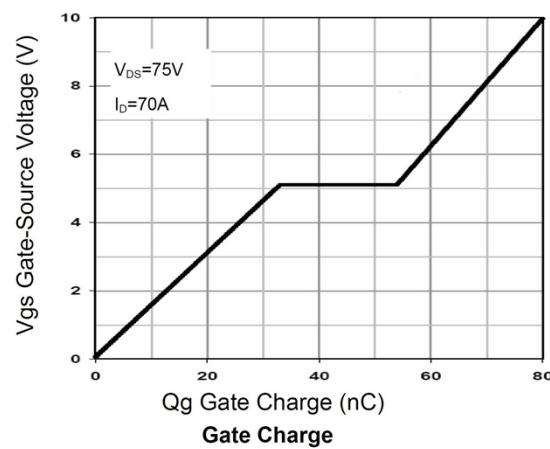
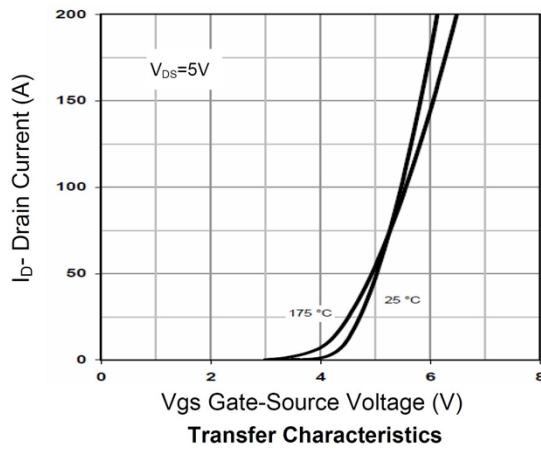
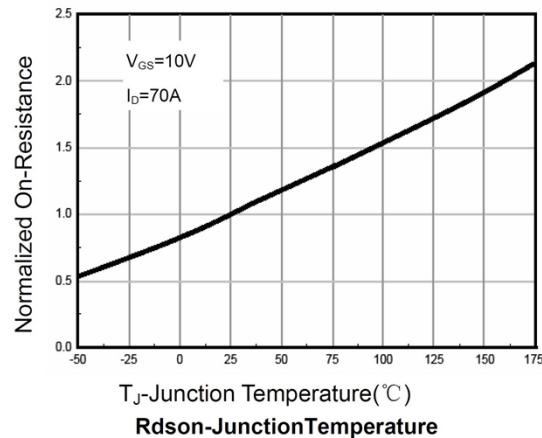
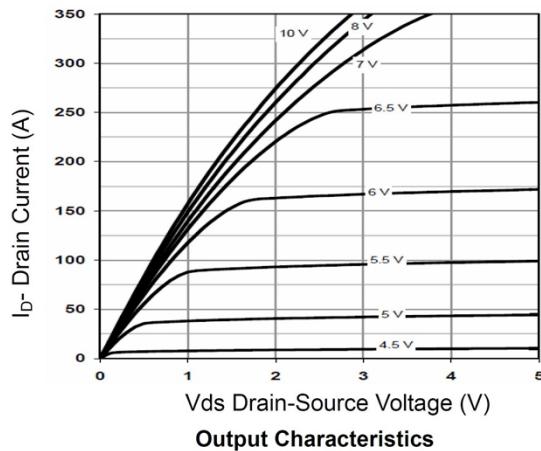
($T_A=25^\circ\text{C}$, unless otherwise noted)

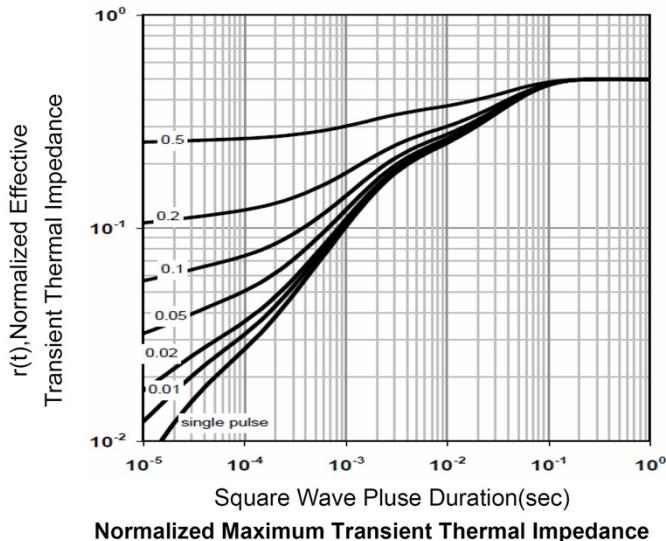
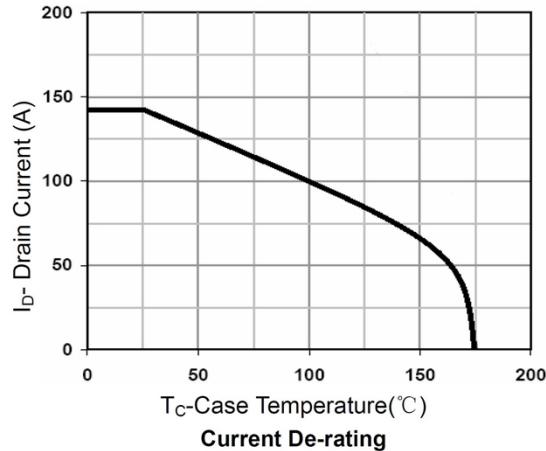
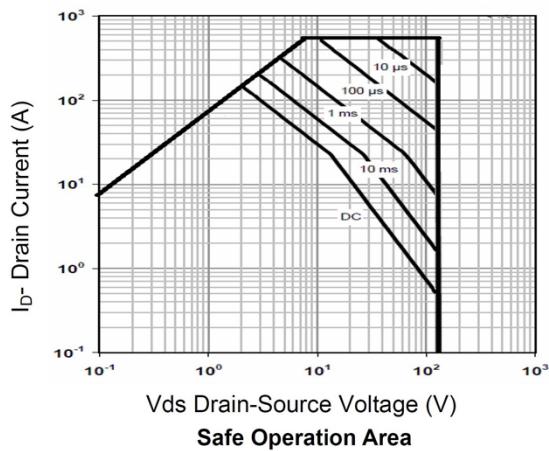
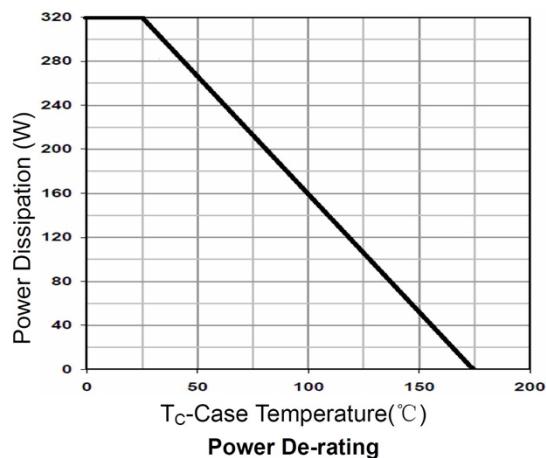
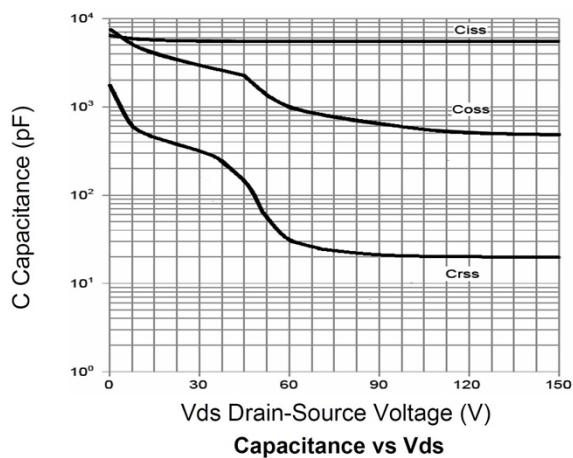
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	150			V
Drain Cut-Off Current	I_{DSS}	$V_{\text{DS}} = 120\text{V}, V_{\text{GS}} = 0\text{V}$		1		μA
Gate-body leakage current	I_{GSS}	$V_{\text{GS}} = \pm 20\text{V}, V_{\text{DS}} = 0\text{V}$			± 0.1	μA
Gate threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	2	3	4	V
Drain-Source ON Resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}} = 10\text{V}, I_D = 20\text{A}$		6.7	8.5	Ω
Dynamic characteristics⁴						
Input Capacitance	C_{iss}	$V_{\text{DS}} = 75\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		5280		pF
Output Capacitance	C_{oss}			653		
Reverse Transfer Capacitance	C_{rss}			24		
Switching Characteristics						
Total Gate Charge(4.5V)	Q_g	$V_{\text{DS}} = 75\text{V}, V_{\text{GS}} = 10\text{V}, I_D = 70\text{A}$		80		nC
Gate-Source Charge	Q_{gs}			33		
Gate-Drain Charge	Q_{gd}			21		
Turn-On Delay Time	$T_{\text{d(on)}}$	$V_{\text{GS}} = 10\text{V}, V_{\text{DS}} = 75\text{V}, R_L = 3\Omega, R_G = 4.7\Omega$		26		nS
Rise Time	T_r			35		
Turn-Off Delay Time	$T_{\text{d(off)}}$			45		
Fall Time	T_f			17		
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}, V_{\text{GS}} = 0\text{V}$			1.2	V

Note :

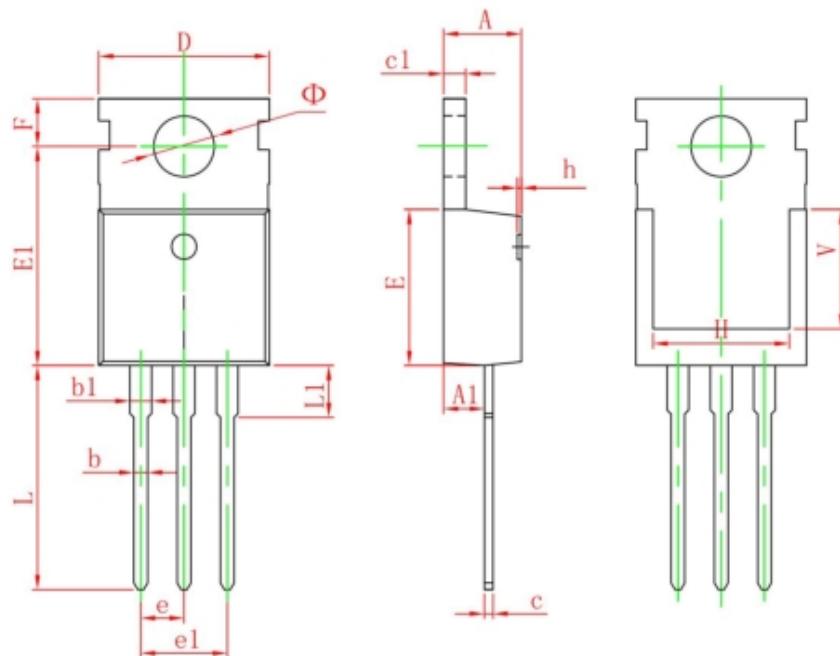
- E_{AS} is tested at starting $T_j = 25^\circ\text{C}, V_{\text{DD}} = 75\text{V}, V_{\text{GS}} = 10\text{V}, L = 0.5\text{mH}, R_g = 25\Omega$;

Typical Characteristics





TO-220-3L-C Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	13.050	0.498	0.514
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276 REF.	
Φ	3.400	3.800	0.134	0.150